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(54) Title: LOW DAMAGE PHOTORESIST STRIP METHOD FOR LOW-K DIELECTRICS

(57) Abstract: Improved methods for stripping photoresist and removing etch-related residues from dielectric materials are provided. In one aspect of the invention, methods involve removing material from a dielectric layer using a hydrogen-based etch process employing a weak oxidizing agent and fluorine-containing compound. Substrate temperature is maintained at a level of about 160 °Cor less, e.g., less than about 90 °C.

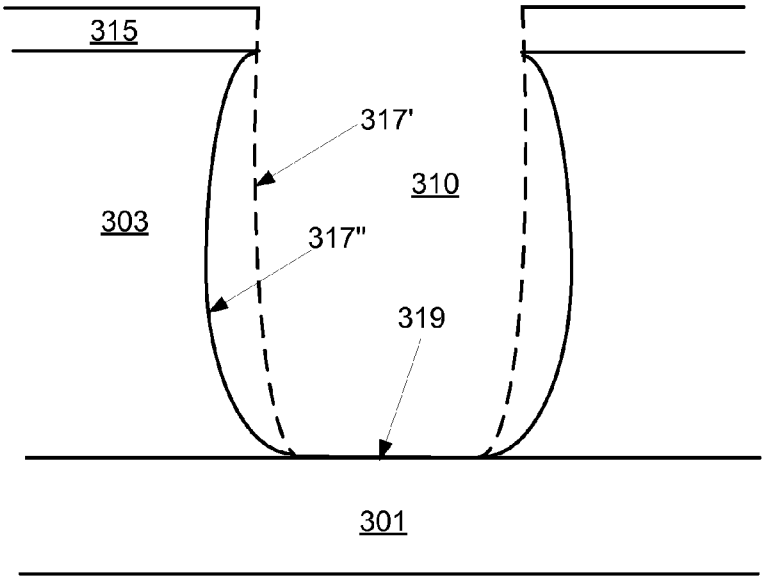


FIGURE 3B

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